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IN SITU APPLICATION OF ETCH BACK FOR IMPROVED DEPOSITION INTO HIGH-ASPECT-RATIO FEATURES

ABSTRACT OF THE DISCLOSURE

A continuous *in situ* process of deposition, etching, and deposition is provided for forming a film on a substrate using a plasma process. The etch-back may be performed without separate plasma activation of the etchant gas. The sequence of deposition, etching, and deposition permits features with high aspect ratios to be filled, while the continuity of the process results in improved uniformity.

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